GlobalOptoisolator™

VDE | UL | CSA | SETI | SEMKO | DEMKO | NEMKO | BABT

6-Pin DIP Optoisolators Transistor Output

CNY17-1
[CTR = 40 – 80%]
CNY17-2*
[CTR = 63 – 125%]
CNY17-3*
[CTR = 100 – 200%]

***Motorola Preferred Devices**

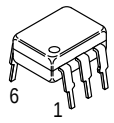
The CNY17–1, CNY17–2 and CNY17–3 devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- Closely Matched Current Transfer Ratio (CTR) to Minimize Unit–to–Unit Variation
- Guaranteed 70 Volt $V_{(BR)CEO}$ Minimum
- ***To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.***

Applications

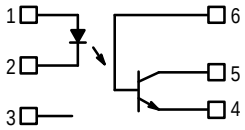
- Feedback Control Circuits, Open Loop Gain Control in Power Supplies
- Interfacing and coupling systems of different potentials and impedances
- General Purpose Switching Circuits
- Monitor and Detection Circuits

STYLE 1 PLASTIC



STANDARD THRU HOLE
CASE 730A–04

SCHEMATIC



PIN 1. LED ANODE
2. LED CATHODE
3. N.C.
4. EMITTER
5. COLLECTOR
6. BASE

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
INPUT LED			
Reverse Voltage	V_R	6	Volts
Forward Current — Continuous	I_F	60	mA
Forward Current — Pk (PW = 1 μs, 330 pps)	I_F(pk)	1.5	A
LED Power Dissipation @ T_A = 25°C with Negligible Power in Output Detector Derate above 25°C	P_D	120 1.41	mW mW/°C
OUTPUT TRANSISTOR			
Collector–Emitter Voltage	V_{CEO}	70	Volts
Emitter–Base Voltage	V_{EBO}	7	Volts
Collector–Base Voltage	V_{CBO}	70	Volts
Collector Current — Continuous	I_C	100	mA
Detector Power Dissipation @ T_A = 25°C with Negligible Power in Input LED Derate above 25°C	P_D	150 1.76	mW mW/°C
TOTAL DEVICE			
Isolation Surge Voltage(1) (Peak ac Voltage, 60 Hz, 1 sec Duration)	V_{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	250 2.94	mW mW/°C
Ambient Operating Temperature Range(2)	T_A	–55 to +100	°C
Storage Temperature Range(2)	T_{stg}	–55 to +150	°C
Soldering Temperature (10 sec, 1/16″ from case)	T_L	260	°C

1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

Preferred devices are Motorola recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)(1)

Characteristic		Symbol	Min	Typ	Max	Unit
INPUT LED						
Forward Voltage (I_F = 60 mA)	T_A = 25°C T_A = –55°C T_A = 100°C	V_F	— — —	1.35 1.5 1.25	1.65 — —	Volts
Reverse Leakage Current (V_R = 6 V)		I_R	—	—	10	µA
Capacitance (V = 0, f = 1 MHz)		C_J	—	18	—	pF
OUTPUT TRANSISTOR						
Collector–Emitter Dark Current (V_{CE} = 10 V, T_A = 25°C)	CNY17–1,2 CNY17–3	I_{CEO}	— —	5 5	50 100	nA
(V_{CE} = 10 V, T_A = 100°C)	All devices	I_{CEO}	—	1.6	—	µA
Collector–Base Dark Current (V_{CB} = 10 V)		I_{CBO}	—	0.5	—	nA
Collector–Emitter Breakdown Voltage (I_C = 1 mA)		$V_{(BR)CEO}$	70	120	—	Volts
Collector–Base Breakdown Voltage (I_C = 100 µA)		$V_{(BR)CBO}$	70	120	—	Volts
Emitter–Base Breakdown Voltage (I_E = 100 µA)		$V_{(BR)EBO}$	7	7.8	—	Volts
DC Current Gain (I_C = 2 mA, V_{CE} = 5 V) (Typical Value)		hFE	—	400	—	—
Collector–Emitter Capacitance (f = 1 MHz, V_{CE} = 0)		C_{CE}	—	8	—	pF
Collector–Base Capacitance (f = 1 MHz, V_{CB} = 0)		C_{CB}	—	21	—	pF
Emitter–Base Capacitance (f = 1 MHz, V_{EB} = 0)		C_{EB}	—	8	—	pF
COUPLED						
Output Collector Current (I_F = 10 mA, V_{CE} = 5 V)	CNY17–1 CNY17–2 CNY17–3	I_C (CTR)(2)	4 (40) 6.3 (63) 10 (100)	6 (60) 10 (100) 15 (150)	8 (80) 12.5 (125) 20 (200)	mA (%)
Collector–Emitter Saturation Voltage (I_C = 2.5 mA, I_F = 10 mA)		$V_{CE(sat)}$	—	0.18	0.4	Volts
Delay Time (I_F = 10 mA, V_{CC} = 5 V, R_L = 75 Ω, Figure 11)		t_d	—	1.6	5.6	µs
Rise Time (I_F = 10 mA, V_{CC} = 5 V, R_L = 75 Ω, Figure 11)		t_r	—	1.6	4	µs
Storage Time (I_F = 10 mA, V_{CC} = 5 V, R_L = 75 Ω, Figure 11)		t_s	—	0.7	4.1	µs
Fall Time (I_F = 10 mA, V_{CC} = 5 V, R_L = 75 Ω, Figure 11)		t_f	—	2.3	3.5	µs
Delay Time (I_F = 20 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3) (I_F = 10 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3)	 CNY17–1 CNY17–2,3	t_d	 — —	 1.2 1.8	 5.5 8	µs
Rise Time (I_F = 20 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3) (I_F = 10 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3)	 CNY17–1 CNY17–2,3	t_r	 — —	 3.3 5	 4 6	µs
Storage Time (I_F = 20 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3) (I_F = 10 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3)	 CNY17–1 CNY17–2,3	t_s	 — —	 4.4 2, 7	 34 39	µs
Fall Time (I_F = 20 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3) (I_F = 10 mA, V_{CC} = 5 V, R_L = 1 kΩ)(3)	 CNY17–1 CNY17–2,3	t_f	 — —	 9.7 9.4, 20	 20 24	µs
Isolation Voltage (f = 60 Hz, t = 1 sec)(4)		V_{ISO}	7500	—	—	Vac(pk)
Isolation Resistance (V = 500 V)(4)		R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance (V = 0, f = 1 MHz)(4)		C_{ISO}	—	0.2	0.5	pF

1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) = I_C/I_F x 100%.
3. For test circuit setup and waveforms, refer to Figure 11.
4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

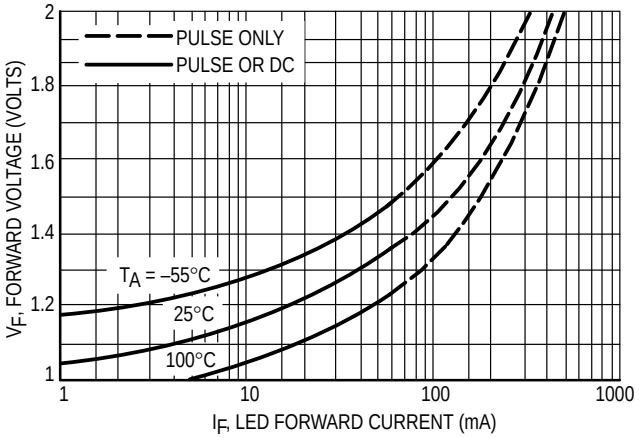


Figure 1. LED Forward Voltage versus Forward Current

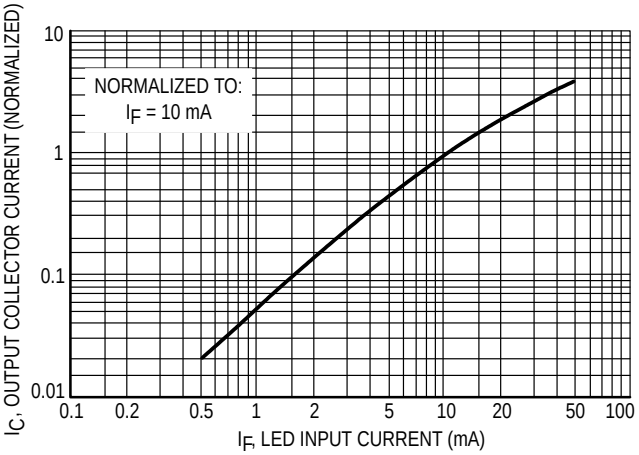


Figure 2. Output Current versus Input Current

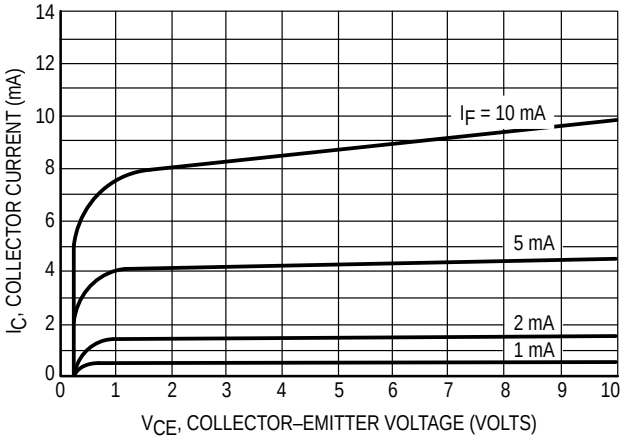


Figure 3. Collector Current versus Collector–Emitter Voltage

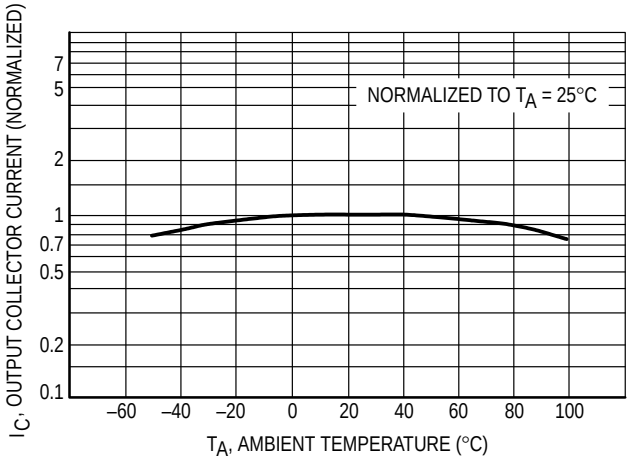


Figure 4. Output Current versus Ambient Temperature

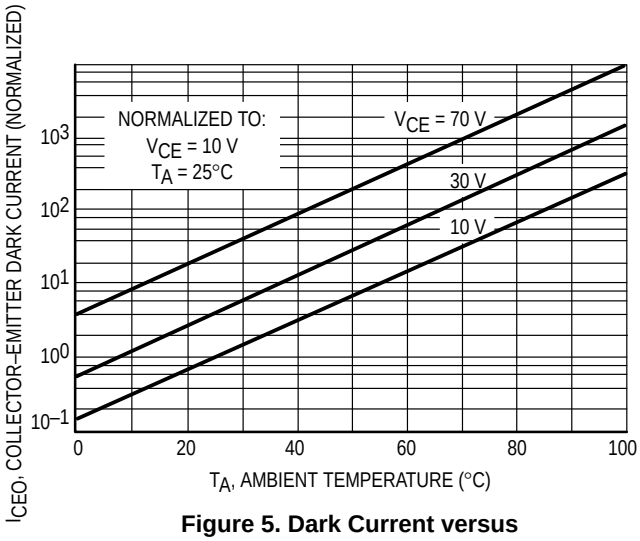


Figure 5. Dark Current versus Ambient Temperature

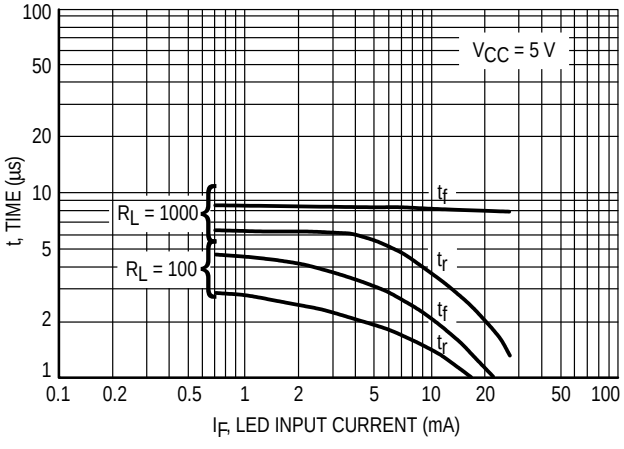


Figure 6. Rise and Fall Times CNY17–1 and CNY17–2

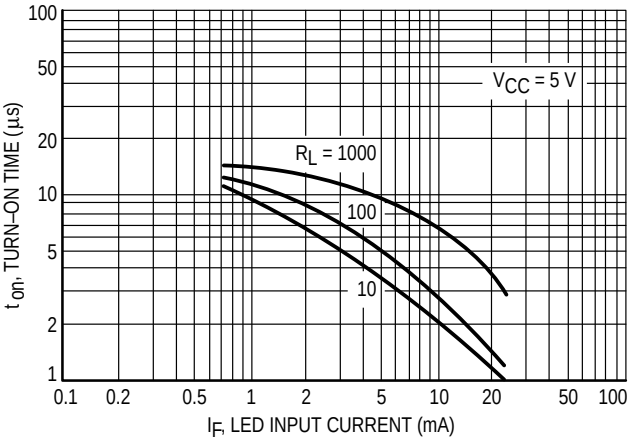


Figure 7. Turn–On Switching Times

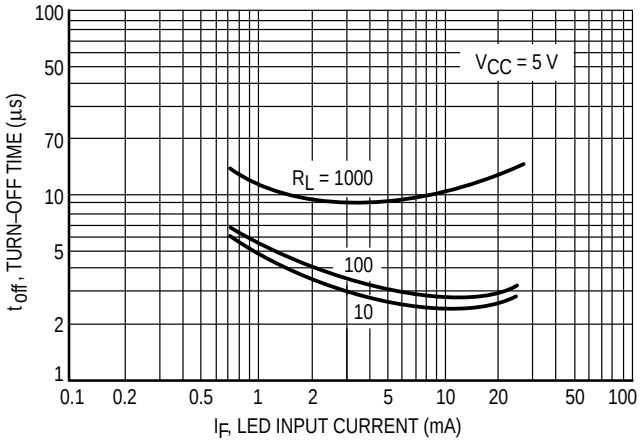


Figure 8. Turn–Off Switching Times CNY17–1 and CNY17–2

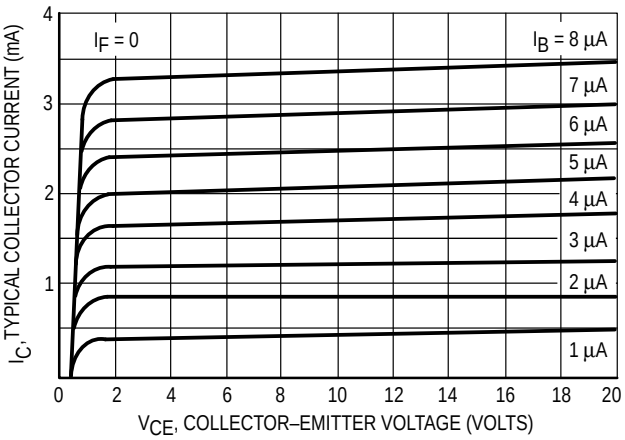


Figure 9. DC Current Gain (Detector Only)

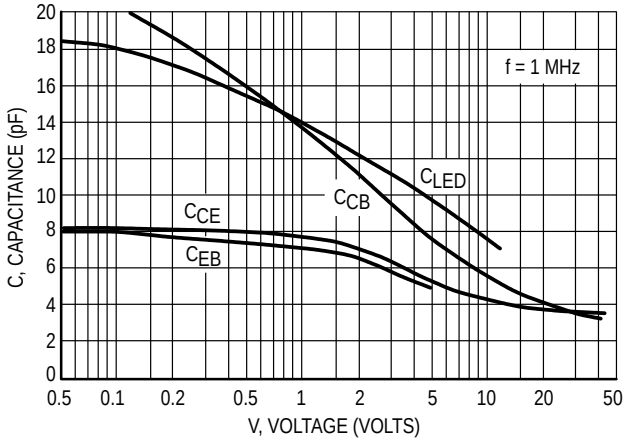


Figure 10. Capacitances versus Voltage

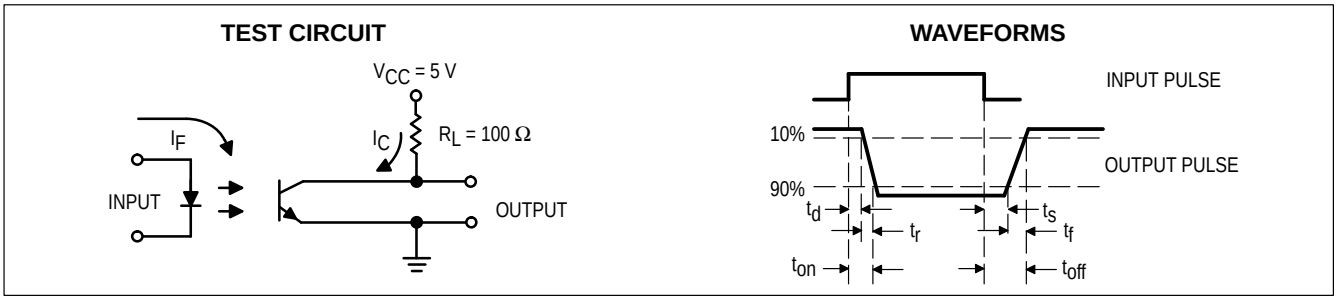
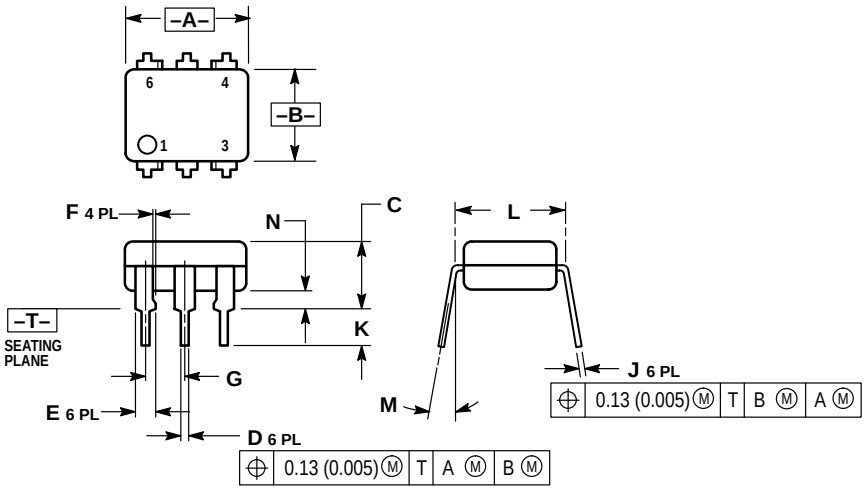


Figure 11. Switching Time Test Circuit and Waveforms

PACKAGE DIMENSIONS

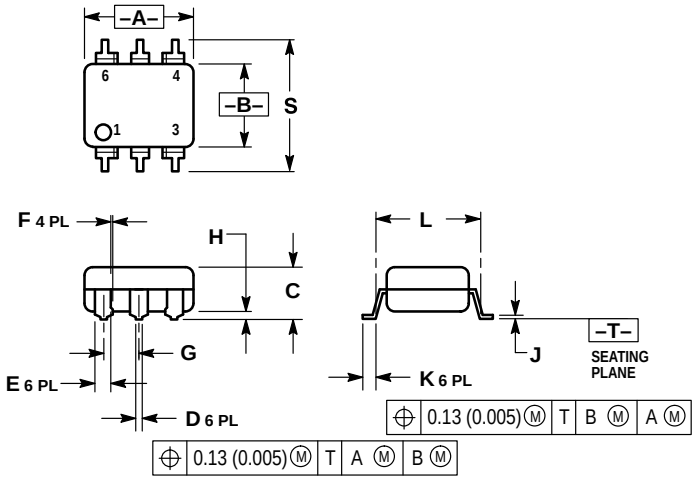


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.015	0.100	0.38	2.54

STYLE 1:
PIN 1. ANODE
2. CATHODE
3. NC
4. EMITTER
5. COLLECTOR
6. BASE

CASE 730A–04
ISSUE G



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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
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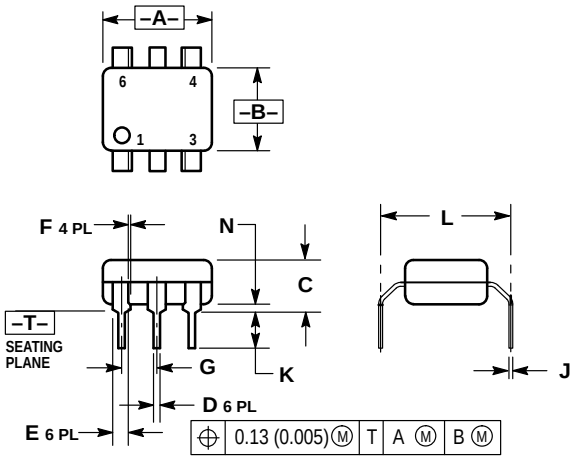
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
H	0.020	0.025	0.51	0.63
J	0.008	0.012	0.20	0.30
K	0.006	0.035	0.16	0.88
L	0.320 BSC		8.13 BSC	
S	0.332	0.390	8.43	9.90

***Consult factory for leadform option availability**

CASE 730C–04
ISSUE D



NOTES:
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2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.400	0.425	10.16	10.80
N	0.015	0.040	0.38	1.02

***Consult factory for leadform option availability**

CASE 730D–05
ISSUE D

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